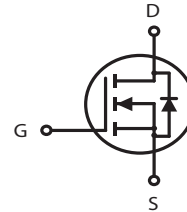


**N-Channel Logic Level Enhancement Mode Field Effect Transistor****PRODUCT SUMMARY**

V _{DSS}	I _D	R _{DS(ON)} (mΩ) Max
80V	25A	35 @ V _{GS} =10V
		50 @ V _{GS} =4.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- TO-252 and TO-251 Package.

**ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise noted)**

Symbol	Parameter	Limit	Units
V _{DS}	Drain-Source Voltage	80	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous ^a	25	A
I _{DM}	-Pulsed ^b	100	A
E _{AS}	Avalanche Energy ^c	196	mJ
P _D	Maximum Power Dissipation ^a	62.5	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C

THERMAL CHARACTERISTICS

R _{θJC}	Thermal Resistance, Junction-to-Case	2	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	50	°C/W

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ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	80			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =64V , V _{GS} =0V			1	A
I _{GSS}	Gate-Body leakage current	V _{GS} = ±20V , V _{DS} =0V			±100	nA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1		3	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V , I _D =16A		25	35	m ohm
		V _{GS} =4.5V , I _D =14A		32	50	m ohm
g _{FS}	Forward Transconductance	V _{DS} =10V , I _D =16A		38		S
DYNAMIC CHARACTERISTICS^b						
C _{ISS}	Input Capacitance	V _{DS} =25V, V _{GS} =0V f=1.0MHz		3270		pF
C _{OSS}	Output Capacitance			210		pF
C _{RSS}	Reverse Transfer Capacitance			145		pF
SWITCHING CHARACTERISTICS^b						
t _{D(ON)}	Turn-On DelayTime	V _{DD} =40V I _D =16A		66		ns
t _r	Rise Time			166		ns
t _{D(OFF)}	Turn-Off DelayTime	V _{GS} =10V R _{GEN} =60 ohm		222		ns
t _f	Fall Time			55		ns
Q _g	Total Gate Charge	V _{DS} =64V, I _D =16A, V _{GS} =10V		50		nC
Q _{gs}	Gate-Source Charge	V _{DS} =64V, I _D =16A, V _{GS} =10V		6		nC
Q _{gd}	Gate-Drain Charge			16		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
I _S	Maximum Continuous Drain-Source Diode Forward Current				16	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =16A		0.9	1.3	V

Notes

- a. Pulse Test: Pulse Width ≤ 300us, Duty Cicle ≤ 2%.
 b. Guaranteed by design, not subject to production testing.
 c. Starting T_J=25°C, L=0.5mH, V_{DD} = 40V. (See Figure13)

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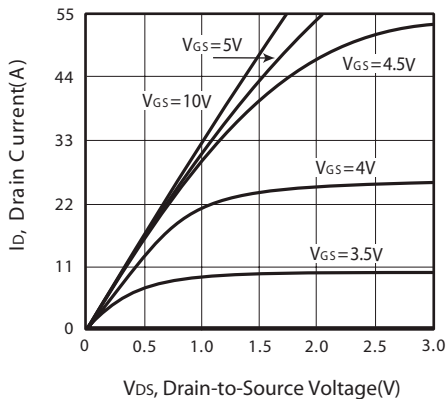


Figure 1. Output Characteristics

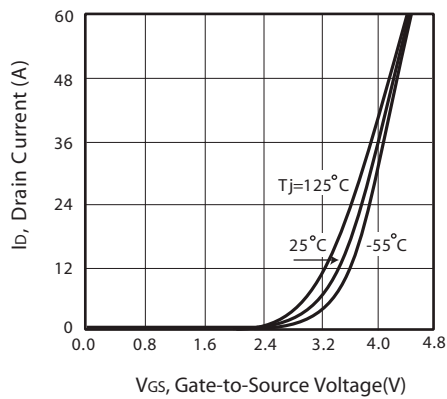


Figure 2. Transfer Characteristics

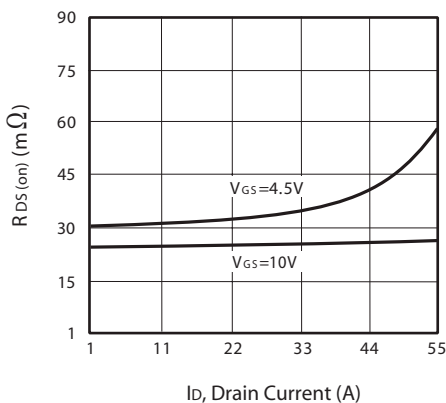


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

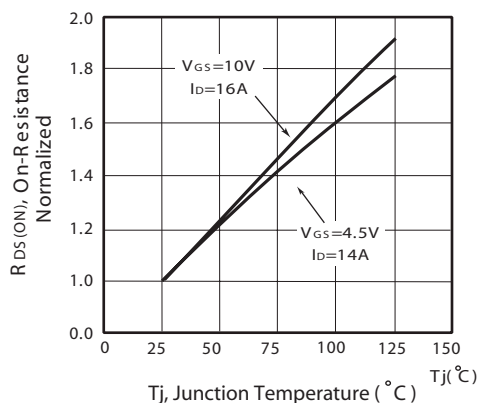


Figure 4. On-Resistance Variation with Drain Current and Temperature

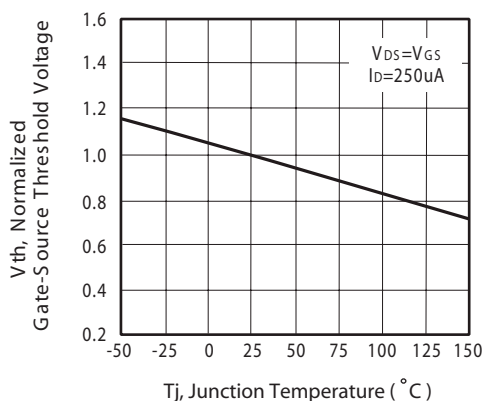


Figure 5. Gate Threshold Variation with Temperature

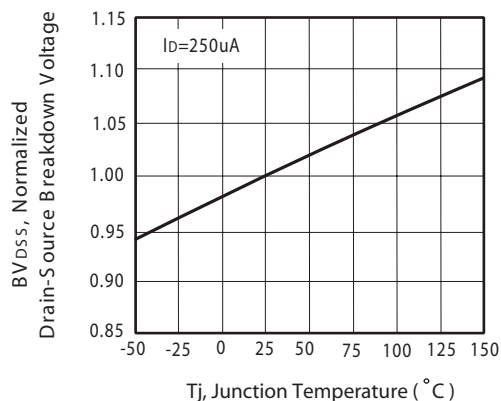


Figure 6. Breakdown Voltage Variation with Temperature

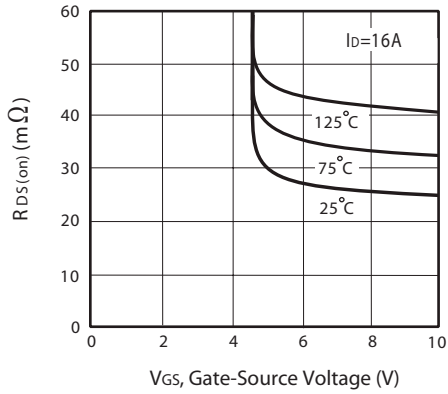


Figure 7. On-Resistance vs. Gate-Source Voltage

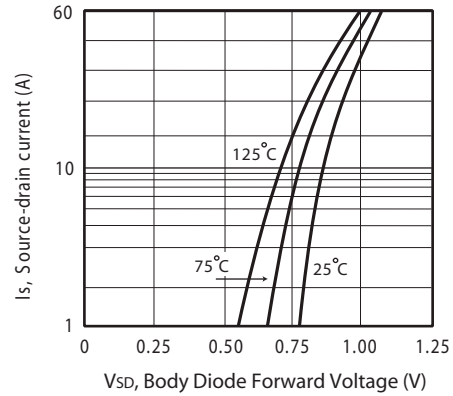


Figure 8. Body Diode Forward Voltage Variation with Source Current

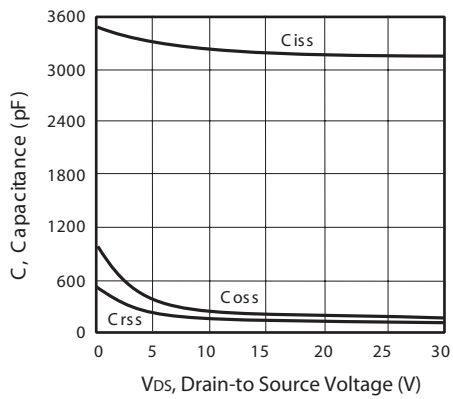


Figure 9. Capacitance

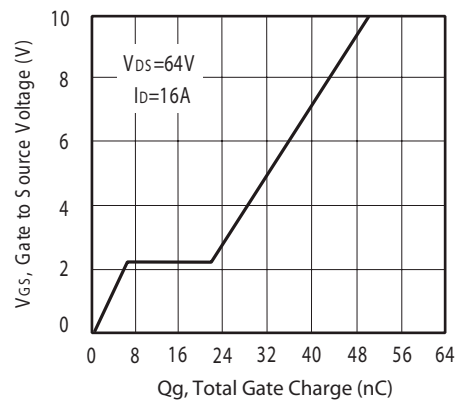


Figure 10. Gate Charge

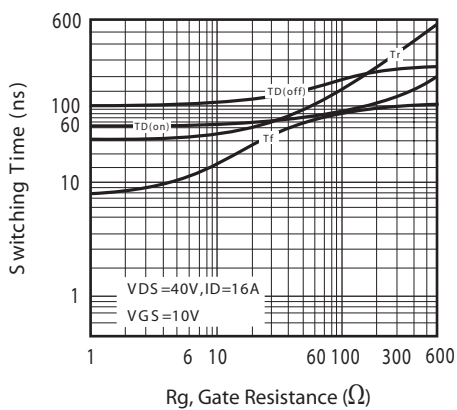


Figure 11. Switching Characteristics

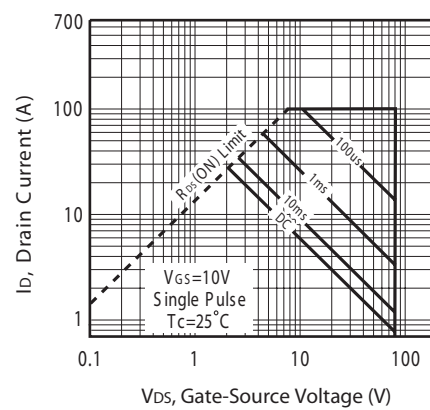
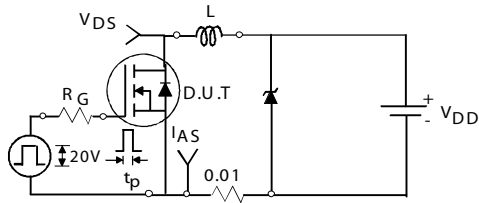
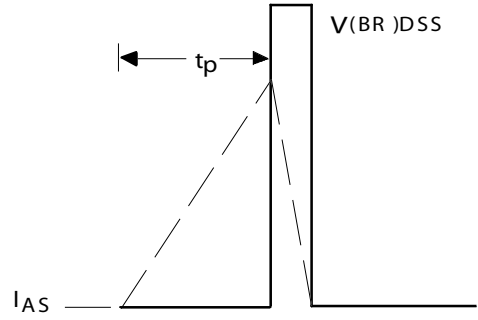


Figure 12. Maximum Safe Operating Area



Unclamped Inductive Test Circuit

Figure 13a.



Unclamped Inductive Waveforms

Figure 13b.

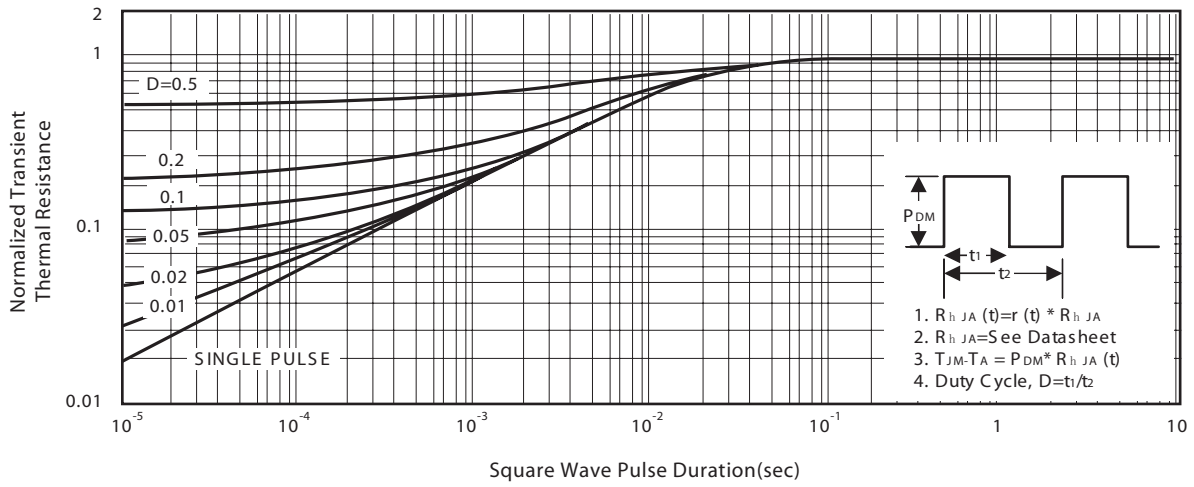
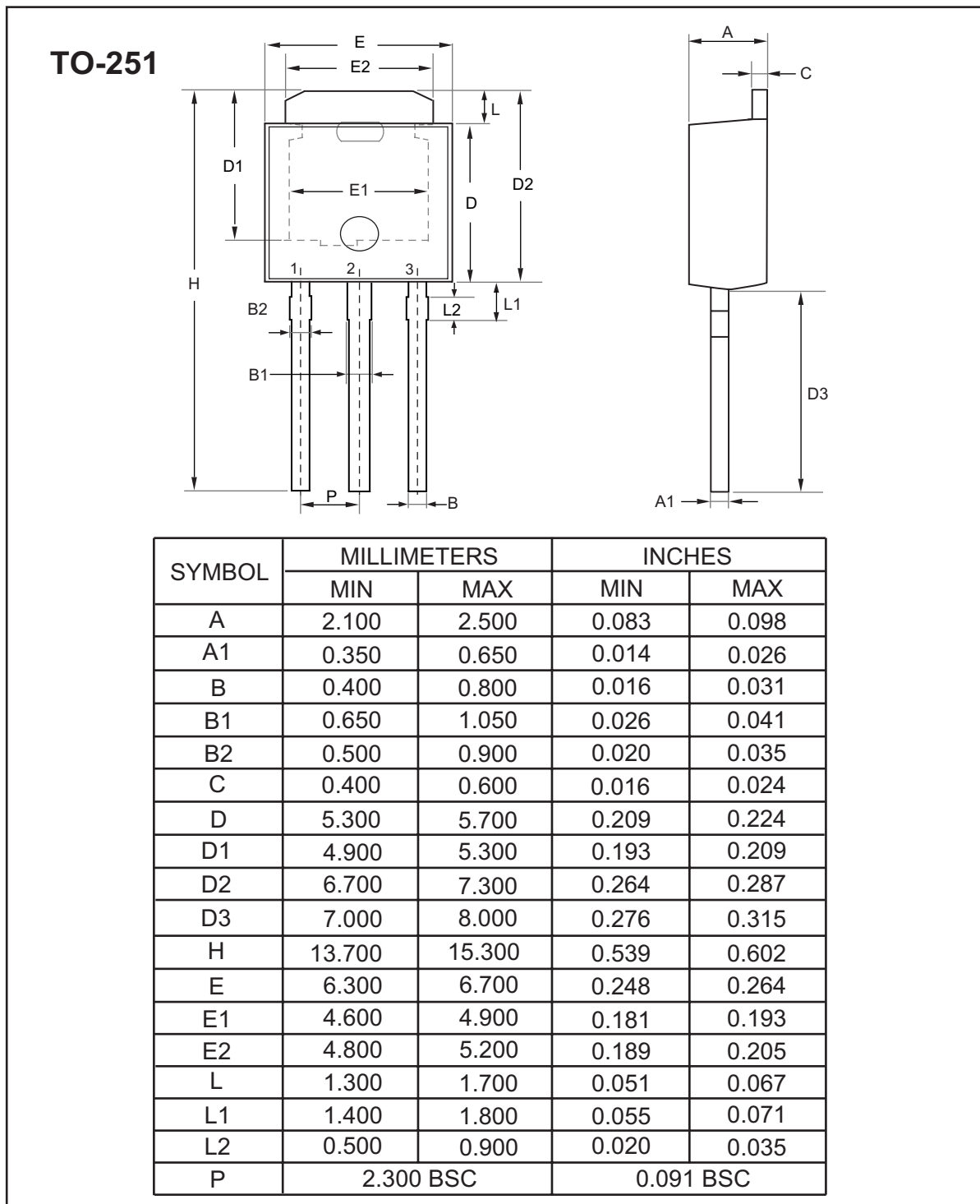


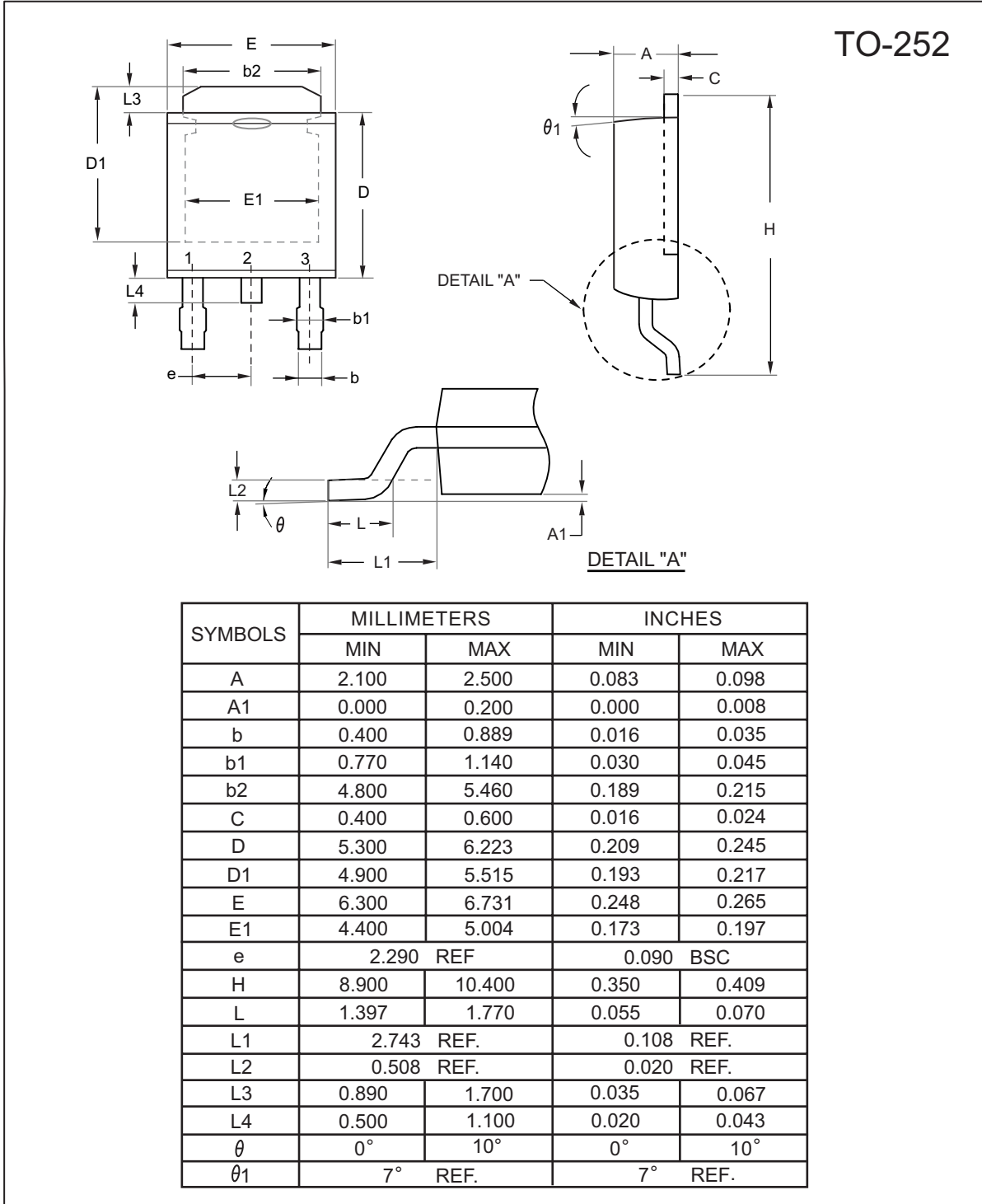
Figure 14. Normalized Thermal Transient Impedance Curve

PACKAGE OUTLINE DIMENSIONS



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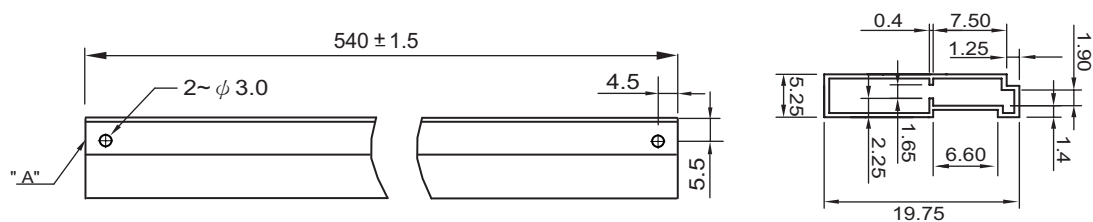
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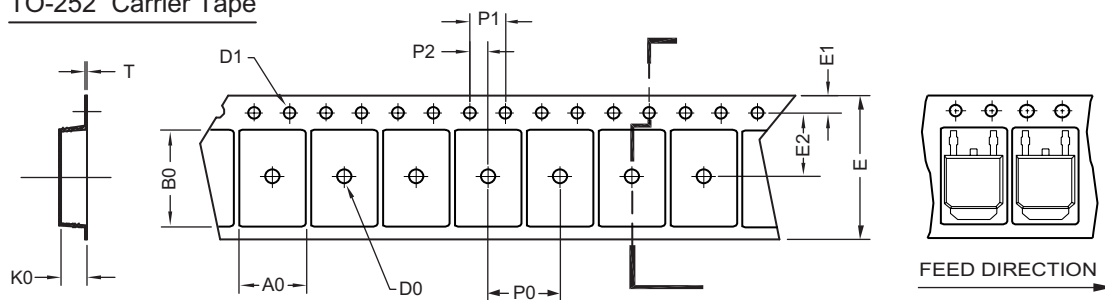
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TO251 Tube/TO-252 Tape and Reel Data

TO-251 Tube



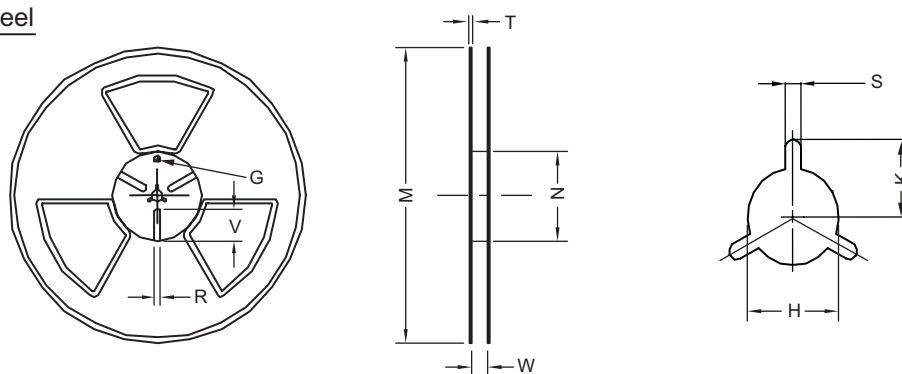
TO-252 Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252 (16 mm)	6.96 ±0.1	10.49 ±0.1	2.79 ±0.1	φ2	φ1.5 +0.1 -0	16.0 ±0.3	1.75 ±0.1	7.5 ±0.15	8.0 ±0.1	4.0 ±0.1	2.0 ±0.15	0.3 ±0.05

TO-252 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 mm	φ 330	φ 330 ±0.5	φ 97 ±1.0	17.0 +1.5 -0	2.2	φ 13.0 +0.5 -0.2	10.6	2.0 ±0.5	---	---	---